



## General Description

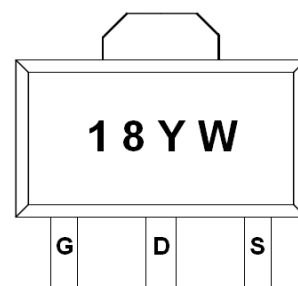
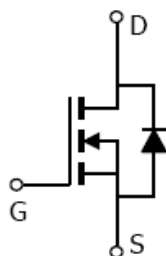
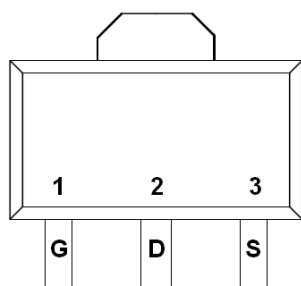
AFN8918, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

## Features

- 40V/4.6A,  $R_{DS(ON)}=30m\Omega@V_{GS}=10V$
- 40V/3.6A,  $R_{DS(ON)}=54m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- SOT-89-3L package design

## Pin Description ( SOT-89-3L )



## Application

- Motor and Load Control
- Power Management in White LED System
- Push Pull Converter
- LCD TV Inverter & AD/DC Inverter Systems.

## Pin Define

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

## Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN8918S89RG	18YW	SOT-89-3L	Tape & Reel	1000 EA

- ※ 18 parts code
- ※ Y year code ( 0 ~ 9 )
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFN8918S89RG : 7" Tape & Reel ; Pb- Free ; Halogen- Free



### Absolute Maximum Ratings

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	4.6
		T <sub>A</sub> =70°C	3.6
Pulsed Drain Current	I <sub>DM</sub>	10	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	1.6	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	1.45
		T <sub>A</sub> =70°C	0.6
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W

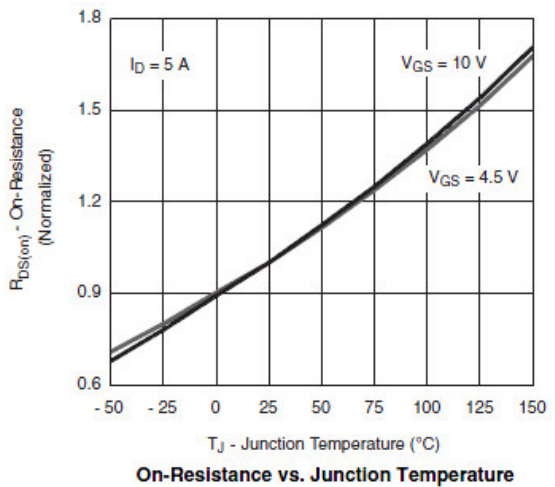
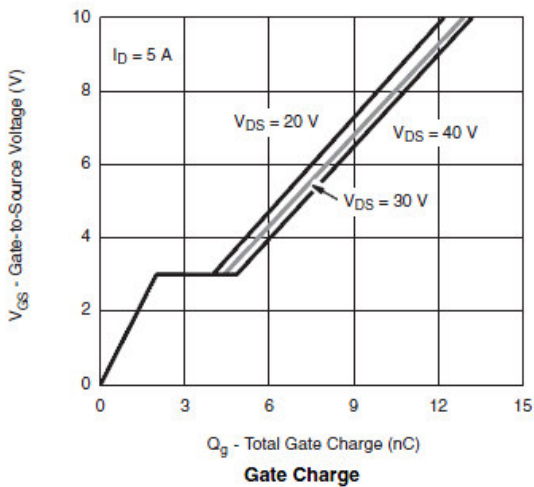
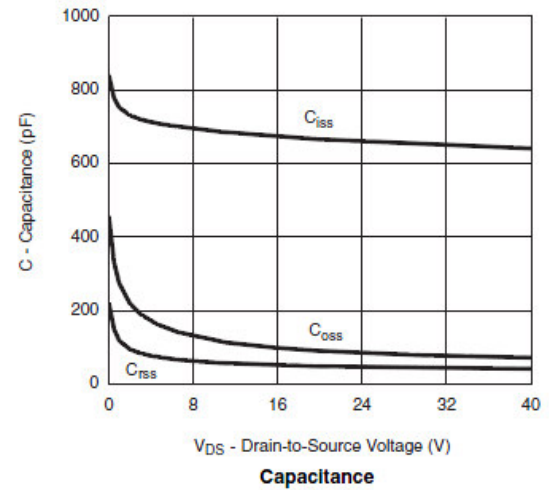
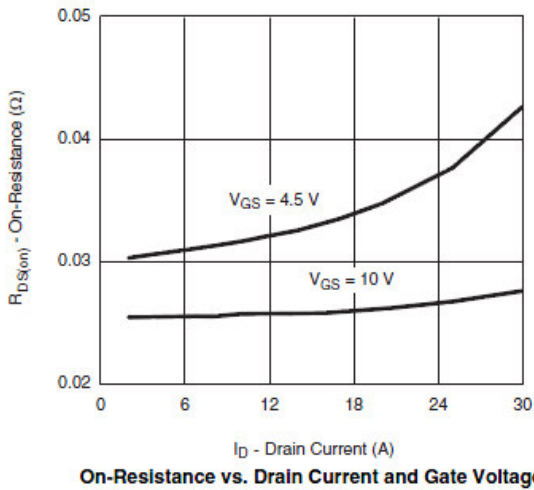
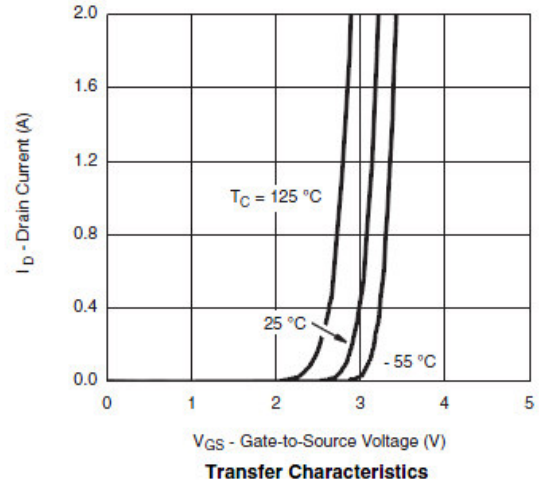
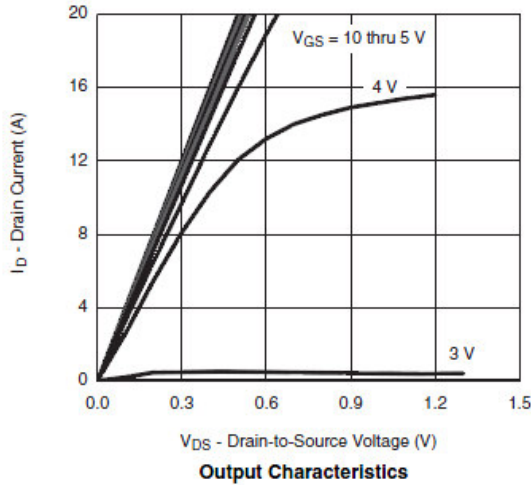
### Electrical Characteristics

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.5		3.0	V
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =40V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			10	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> =10V	20			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =4.6A		24	30	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.6A		42	54	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =5.0A		25		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =2A, V <sub>GS</sub> =0V		0.85	1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V I <sub>D</sub> = 3A		10	14	nC
Gate-Source Charge	Q <sub>gs</sub>			2.8		
Gate-Drain Charge	Q <sub>gd</sub>			3.2		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V f=1MHz		850		pF
Output Capacitance	C <sub>oss</sub>			110		
Reverse Transfer Capacitance	C <sub>rss</sub>			75		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, R <sub>L</sub> =4Ω I <sub>D</sub> ≧3.0A, V <sub>GEN</sub> =10V R <sub>G</sub> =1Ω		6	12	ns
	t <sub>r</sub>			10	20	
Turn-Off Time	t <sub>d(off)</sub>			20	36	
	t <sub>f</sub>			6	12	

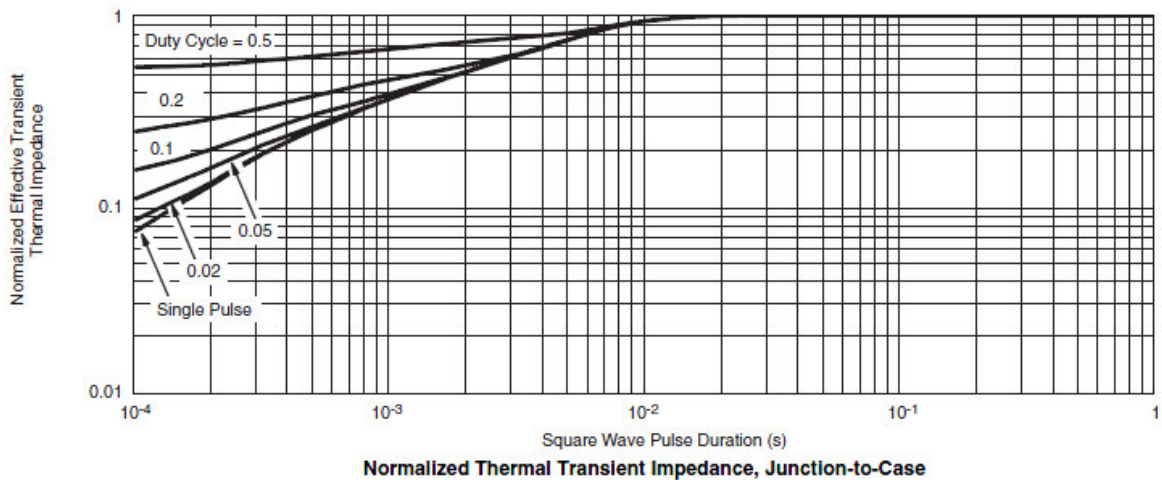
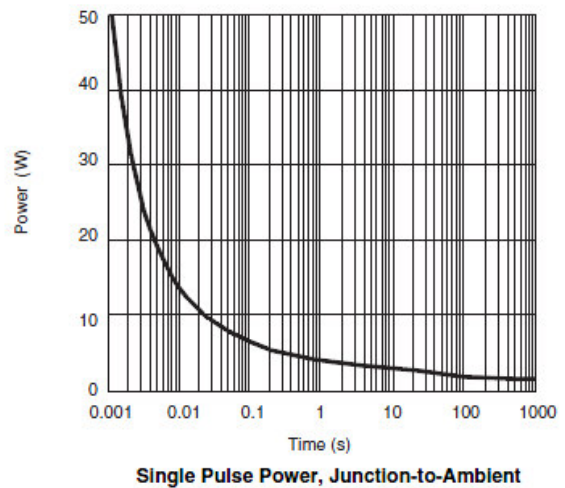
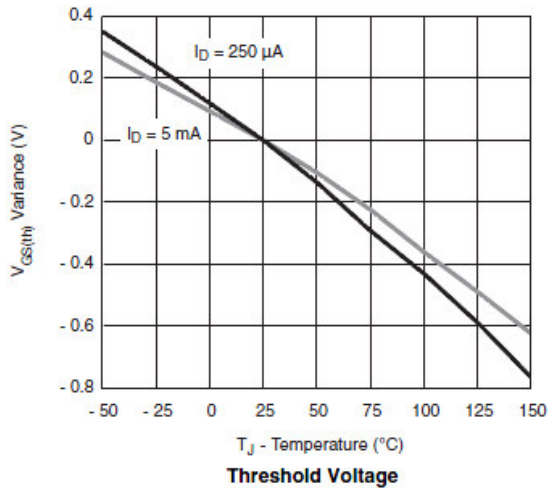
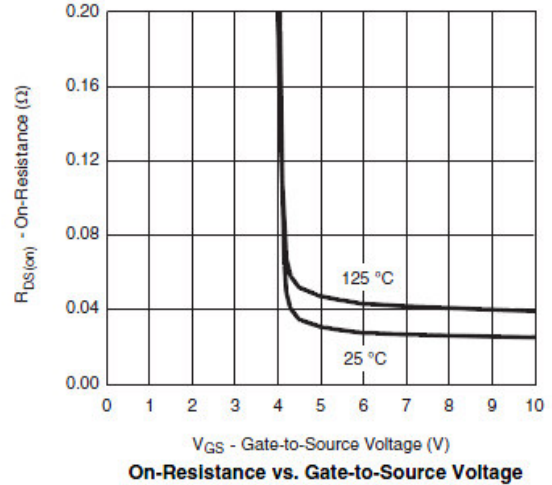
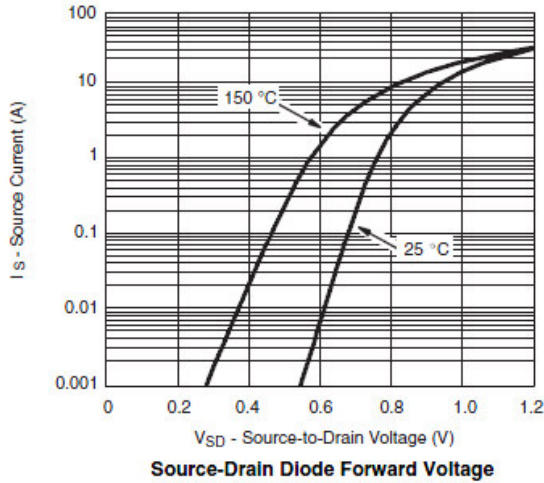


## Typical Characteristics





## Typical Characteristics





**Typical Characteristics**

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

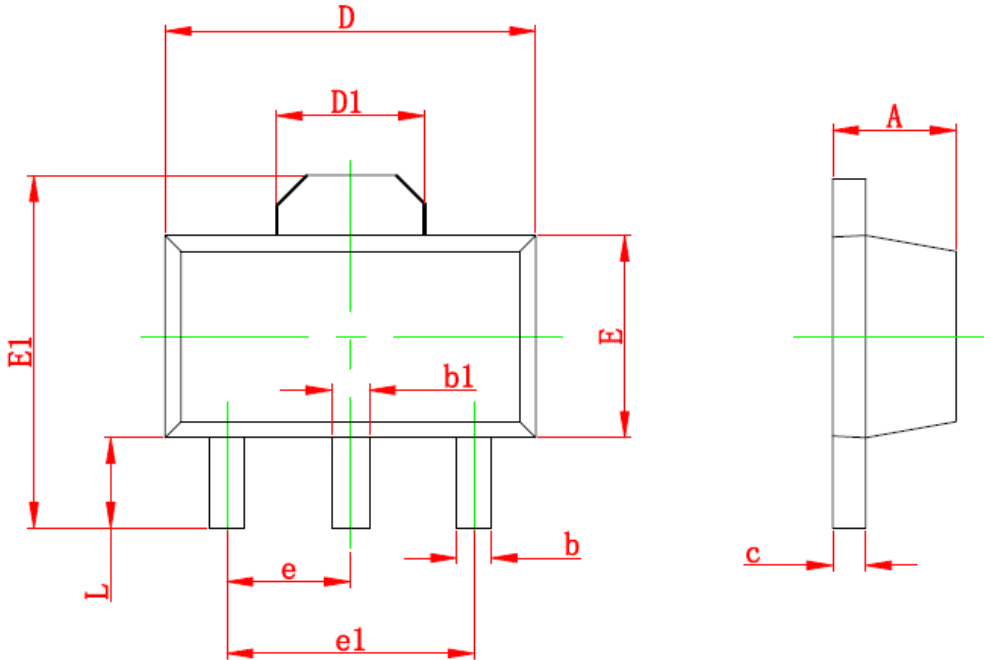


Unclamped Inductive Switching Test Circuit & Waveforms





**Package Information ( SOT-89-3L )**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.197
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP		0.060TYP	
e1	3.000 TYP		0.118TYP	
L	0.900	1.200	0.035	0.047

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